

A DLTS study of 4H-SiC-based p-n junctions fabricated by boron implantation

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Impurity interaction with point defects in the Si-SiO₂ structures and its influence on the interface properties

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Investigation of strain relaxation mechanism in Si-SiO₂ system during the process of its formation

Kropman, Daniel; Poll, V.; Kämer, T.; Ugaste, Ülo; **Melikov, Enn**; Arbu, Uno; Paomets, V. Physica status solidi (a) 2003 / 2, p. 297-301 <https://onlinelibrary.wiley.com/doi/abs/10.1002/pssa.200306611>

Simulations of wide bandgap SiC N-N heterostructure diode

Patankar, Udayan Sunil; Koel, Ants; Pardy, Tamas 2020 IEEE International Conference on Consumer Electronics (ICCE), Las Vegas, NV, USA, January 4-6, 2020 2020 / 4 p <https://doi.org/10.1109/ICCE46568.2020.9043130>

Structure-reactivity relationships for organosilicon compounds revisited

Ploom, Anu; Tuulmets, Ants ISOS XVII Berlin 2014 : the 17th International Symposium on Silicon Chemistry jointly with the 7th European Silicon Days : Berlin, August 3-8, 2014 2014

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Создание и свойства высокоомных эпитаксиальных слоев кремния большой площади

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